

5b	5a	Vb - Vb'	,	
6a		1	,	
6b	6a	Vlb - Vlb'	,	
7a		1	,	
7b	7a	IIb - IIb'	,	
8a		1	,	
8b	8a	VIIIb - VIIIb'	,	
9		2	,	
10	11	9 X - X' XI - XI'	,	
12a			,	
12b	12a	XIIb - XIIb'	,	
13, 14, 15		12a XIIb - XIIb'		12b
		,		
16a	15		,	
16b	16a	XVIb - XVIb'	,	
17a	16a			
17b	17a	XVIIb - XVIIb'	,	
18		3		
,				
19	20	18 XIX - XIX' XX - XX'	,	
21a	21c	3	(	)
		,		
22		4	,	
23	24	22 XXIII - XXIII' XXIV - XXIV'		
25		5	.	

가

가

가

가

가

(가

$$),$$

(vertically aliened mode)

가

가

가

가

가

가

가

가

가

[illegible]

(171), (173) (131) 가 (154)
 (140) , , (R, G, B)가 (R, G, B)
 , (R, G, B)가 (171) , 가
 (R, G, B) (121) (171) (125, 179)
 (R, G, B) (154)
 ()
 (R, G, B) SiOC SiOF
 4.0 가 (180) (175) (185) 가 (180)
 (R, G, B) (180) 가
 (180) (171) (179) (182) 가
 (140) (121) (125) (181) 가 (181,
 182) (121) (171) ()
 , (180)
 (180) ITO(indium tin oxide) IZO(indium zinc oxide)
 (191) (191) (185) (175)
 (191) (200) (270)
 , 가 (3)
 (191) (270)
 (191) (121) (171) (aperture ratio)
 , (131) (175)
 , (180) (contact assistant)(81, 82)가 (81, 82)
 (181, 182) (121) (171) (129, 179)
 (81, 82) (121) (171) (129, 179)
 (191) (81, 82)
 , (100) (200) , (110) (210)
 (121) (171) (R) (G) (B) (B) (220)
 (220) (220)
 (131) (121), (171) (131)
 , (220)
 , (220) (220) 가 (131), (121) (171)
 (220) (220)
 ,
 (220) (210) (191)
 (270)

, (320) (220) (270) (320)
 , (3) (310) (40) 가 , (100, 200)
 (11, 21) (3) (100, 200)
 , (200,) (100,
)
 , 4a 4c
 4a (210) , (200)
 (220) (220) 1.5-3.0 μ m 가 ,
 (200)
 , 4b (210) ITO IZO
 (270)
 , 4c (220) (320) (100, 200) (cell gap
) 4.0 μ m (220) 1.5 μ m (350)가 2.5 μ m 가
 , 2 (210) (21)
 ,
 , (220) (131) (220) (220) 가
 .
 , 1 3 5a
 8c 1
 5a 8a 5b 8b 4a 8a
 Vb-Vb, VIb-VIb, VIIb-VIIb, VIIIb-VIIIb'
 , 5a 5b (110) 1,
 000 3,000 (121)
 (131)
 , 6a 6b (140), (150), (160)
 (doped amorphous silicon island)(161) (140) (154)
 , 7a 7b (173) (171),
 (175) (171) (175) 가
 (161) (161) (154) (163, 165)
 , (154) (154)

(R, G, B)

(180) (180) (140) (1

81, 182, 185)

1 2 , 1400 1600 ITO IZO (11)

(190) (81, 82)

5 4

1 2

9 11 2

9 2 X-X' XI-XI' 10 11 9

9 10 11

가 1

9 11 2 (110)

(140) (171)

(131) (121) (121) (12

1) 190) (175) (131) (140) 가 , (

(154) (163, 165)가

(154) (171) (171) (175)

(154) (171) (175)

9 (131) (131) (220)

(220) (131) (220) 가 (131)

(220) (131)

2 12a 17b 9

11

12b 12a XIIb-XIIb'

12b 13, 14, 15 12a XIIb-XIIb'

16b 16a XVIb-XVIb' 16a 15

17a 16a XVIIb-XVIIb' 17a XVIIb-XVIIb'

12a 12b 1,000 3,000

(121) (131)

13 (140), (150), (160)

1,1600 5,000 , 1600 2,000 , 11400 600

(60) 1 μm (170) 2 μm 1,1600 3,000

(A) (61, 62) (210) 가 1 (61) 2 (62)
 (A) 1 (61) 가 (C) (B) (60) 2 (214) (A) (62)
 1 (61) 1/2 , 4,000

(transparent area) (light blocking area) (translucent area)
 (slit) (lattice pattern) 가
 olution) 가 가 (res

14 (160) (B) (170) (170)
 (61, 62) CeNHO3 가 172 (170)

15 (B) (160) (150) (150)
 160 (ashing) (150) 154 (150) (C) 2 (62) 2 (62) (162)
 (162) (C) (172) (171) (163) (175)

16 1 (61) (C) (154) 가 가
 (C) (C) (172) (171) (163) (175)
 165) (A) (162) 1 (61) (C) (172)

(171) (175) , 17a 17b , , (R, G, B)

(C) (C) 가 ,
 (110) (R, G, B) (180) (171) (129, 179)
 (175) (140) (181, 182, 185) (121) (171) (129, 179)

9 11 , 1400 1600 (190) (81, 82) (11)

2 1 (171)
 (163, 165) (154) (173)
 (175)

1 2

가

18 20 3

18 3 19 1

8 XIX-XIX' 20 18 XX-XX XX-XX'

3 1 가 (200) (100)

(100, 200) (3) (100, 200) 가 가 (11, 21)

(320) (3) (40) 가 가 VA(vertically aligned) (200)

(100, 200) (100, 200) (100) TN(twisted nematic)

(100) (110) 가 (gate line)(121)

(121) (resistivity) (Ag) (131) (121) (131)

(Al) (Al alloy) (Cr), (Ti)

(Ta) 가 가 (124) (121)

20-80 °

(131) 가 (191)

(175) (140)

(121) (131) (SiNx) (gate insulating layer)

(140)

(140) (hydrogenated amorphous silicon)

(silicon island)(154)가 (154) 가 가 (124)

(154) (silicide) n (ohmic contact)(163, 163)

165)가 n+

(163, 165) (140) (data line)(171)

(drain electrode)(175) (171) (175) Al

Ag (171) (121) (121) 가

(source electrode)(173) (173) (175) (124)

(163, 165)

(154) (171) (175) (163, 165)

(171), (173) (131) 가 (154)

(140) (R, G, B)가 (R, G, B)

(R, G, B) (171) 가

(R, G, B)가 (171) 가

(R, G, B) (121) (171) (129, 179)

(R, G, B) (150)

() .

(R, G, B) 4.0 가 SiOC SiOF (180)

(180) (175) (185) 가 .

(R, G, B) 가 (180) (171) (179) (182) 가 ,

(140) (121) (129) (181) 가 .

(181, 182) (121) (171) () .

(180) ITO(indium tin oxide) IZO(indium zinc oxide)

(191) (191) (185) (175) .

(191) (200) (270)

, 가 (3) .

(191) (270) .

(191) (121) (171) (aperture ratio) .

, (131) (175) .

, (180) (contact assistant)(81, 82)가 (81, 82)

(181, 182) (121) (171) (129, 179)

. (81, 82) (121) (171) (129, 179)

(191) . (81, 82)

, (100) (200) , (110) (210)

(121) (171) (R) (G) (B) (B)

(154) (220) . (220)

가

(220)가 (210) (191)

(270) .

, (320) (220) (270) (320)

, (3) (3) (40) 가 , (100, 200)

(11, 21) (3) (310) (3) (100, 200) .

, (200,) (100,

) .

, 21a 21c 3 .

21a , (200) ,

(210) 가 . ,

(501) 가 (500) (802)

가

, (220) 1.5-3.0 μm 가 , 가
 , (200)
 , 21b (210) ITO IZO
 (270)
 , 21c (220) (320) (100, 200) (cell gap)
) 4.0 μm (220) 1.5 μm (350)가 2.5 μm 가
 , 19 (210) (21)
 , 5 4
 3
 22 24 4
 22 4 XXIII-III' XXIV-XXIV' 23 24 22
 23 24 가 3
 22 24 (140) 4 (171) (110)
 1) (131) (121) (121) (12
 190) (175) (131) (140) 가 , (1
 , (154) (163, 165)가
 (154) (171) (175) (175)
 (154)
 , 23 (210) (210) (220) 가 가
 (350)
 , 1 4
 가
 25 5
 25 (340) (341) (342)
 (100) (200) (3) 가 ,
 (100) 가 (3) 가 (270)
 (11, 21) (polyide)

ITO(Indium Tantal Oxide) (190) 가 .
 (R), (G), (B) (230)
 . , (B) (230B)

5 (22)
 가 .

(310) 가 가 (3) (270)
 가 (340) .

가

가

, , 가 ,

가

(57)

1.

가 , 30

2.

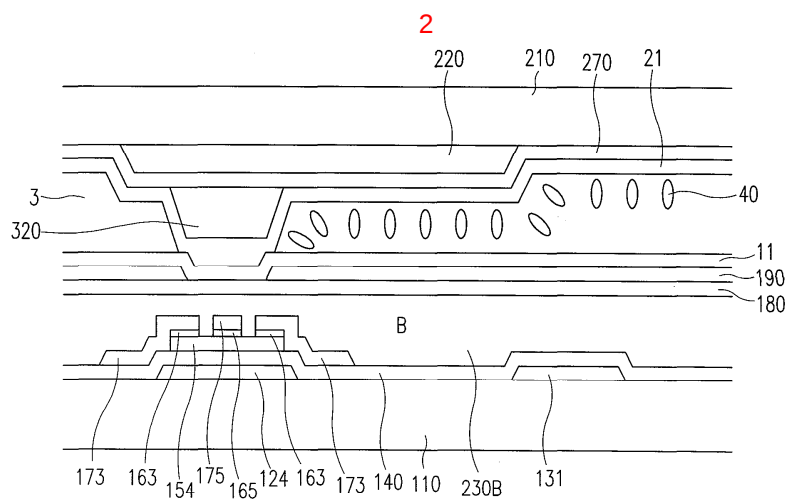
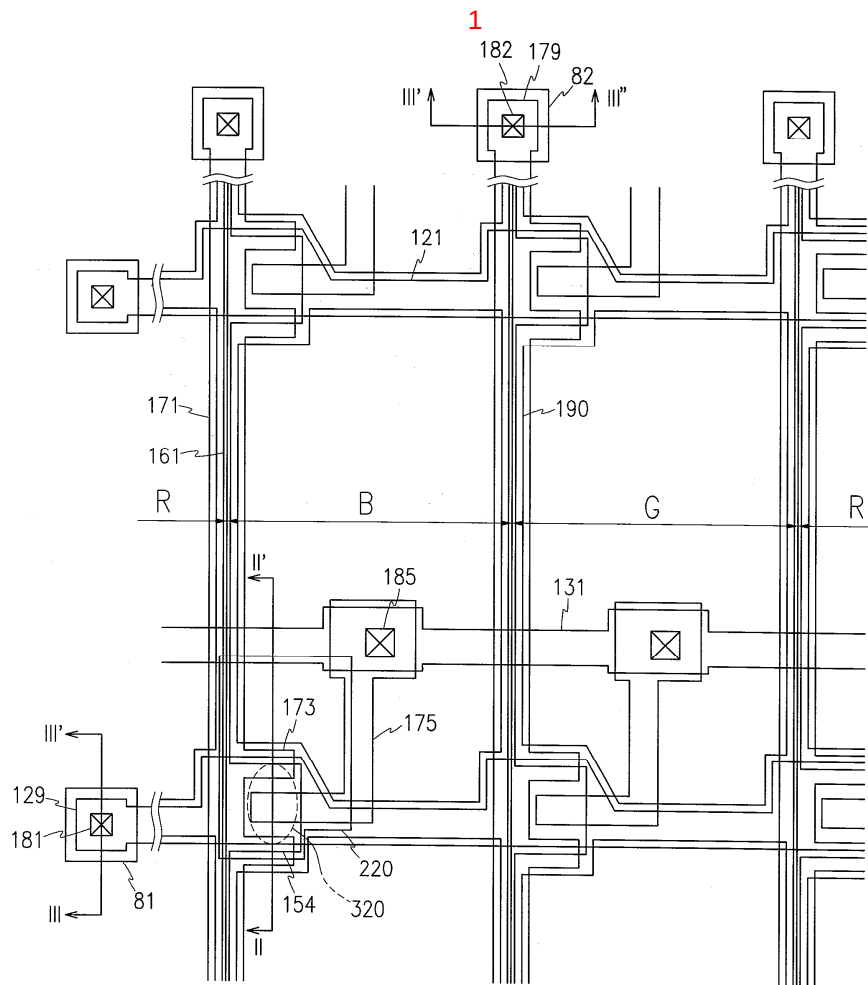
1 ,

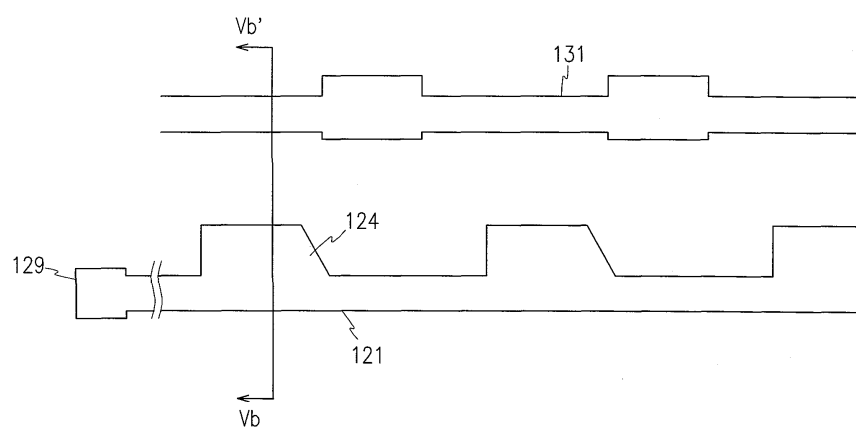
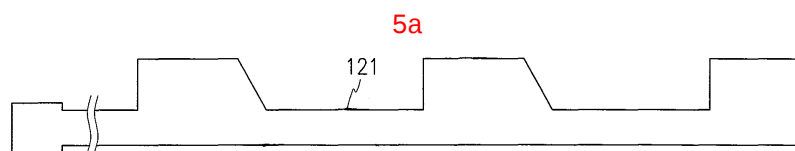
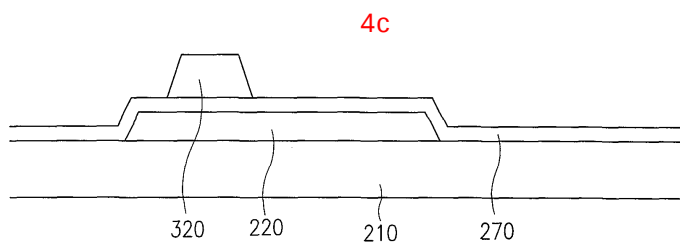
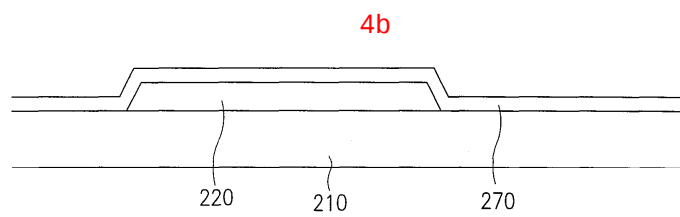
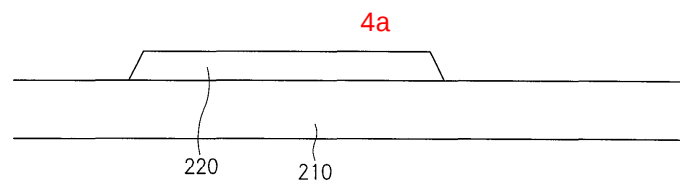
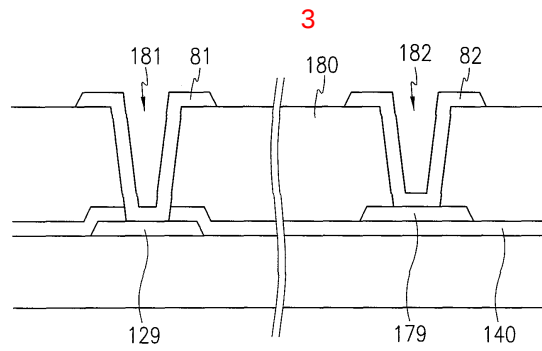
3.

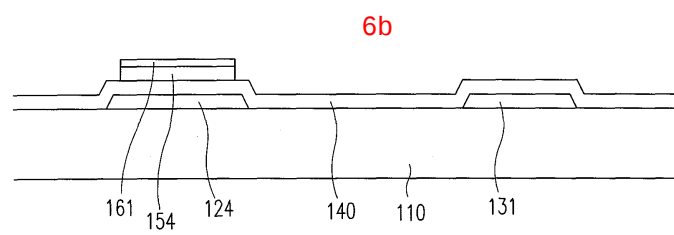
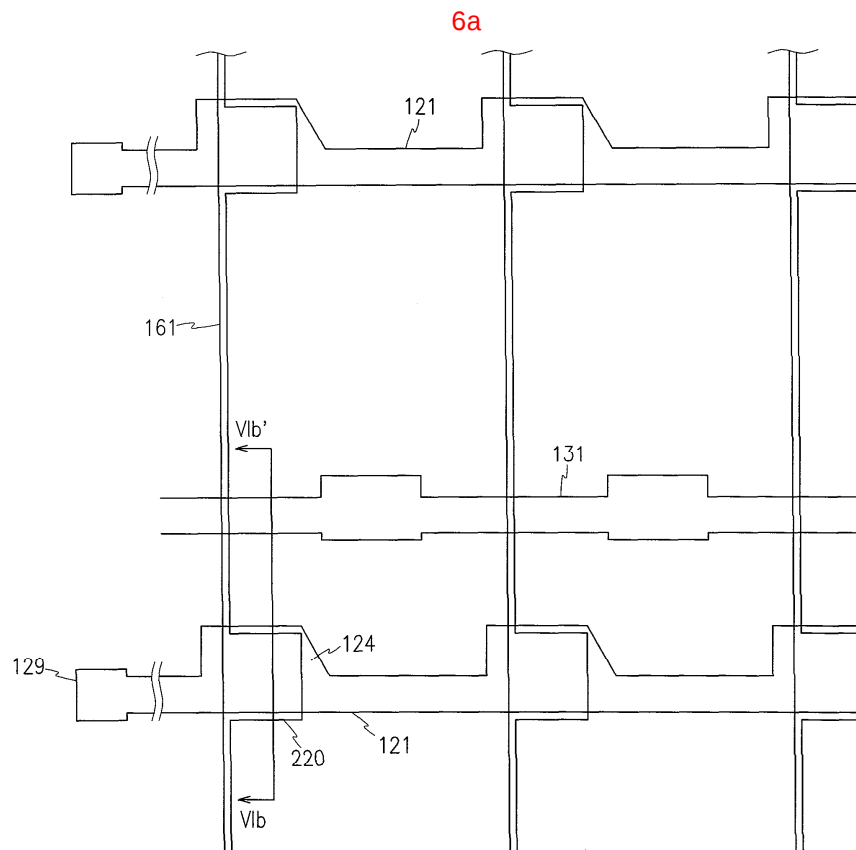
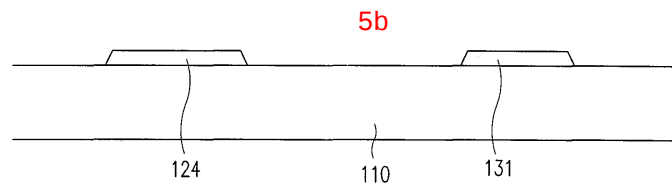
1 ,

가 1 , , 가 1 ,

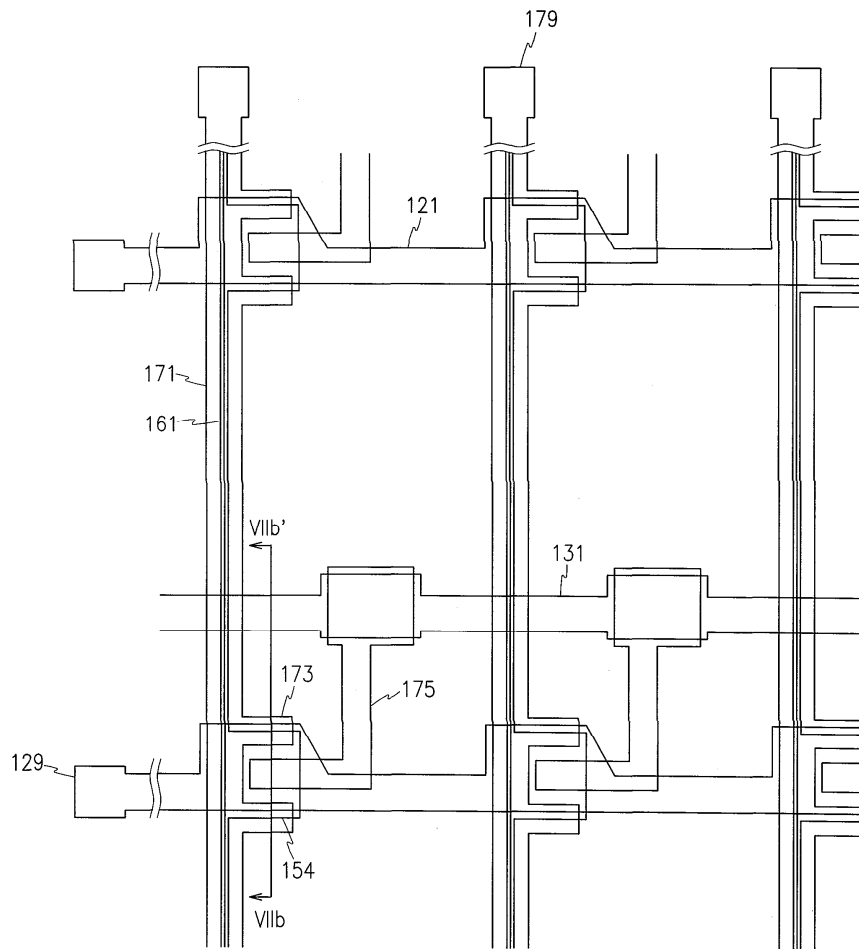
1



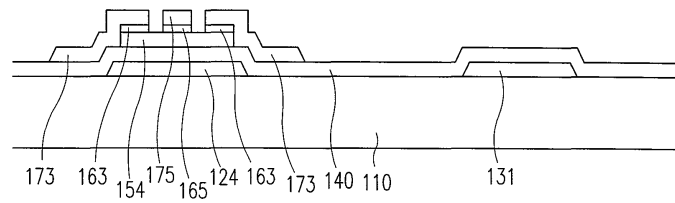


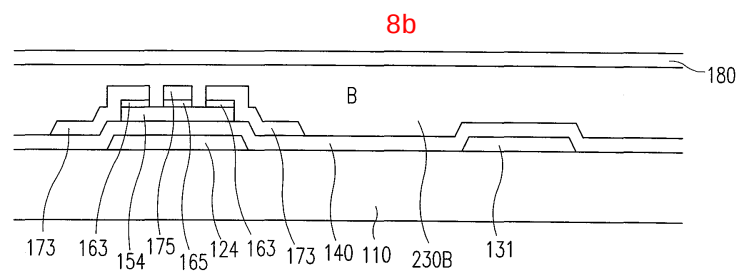
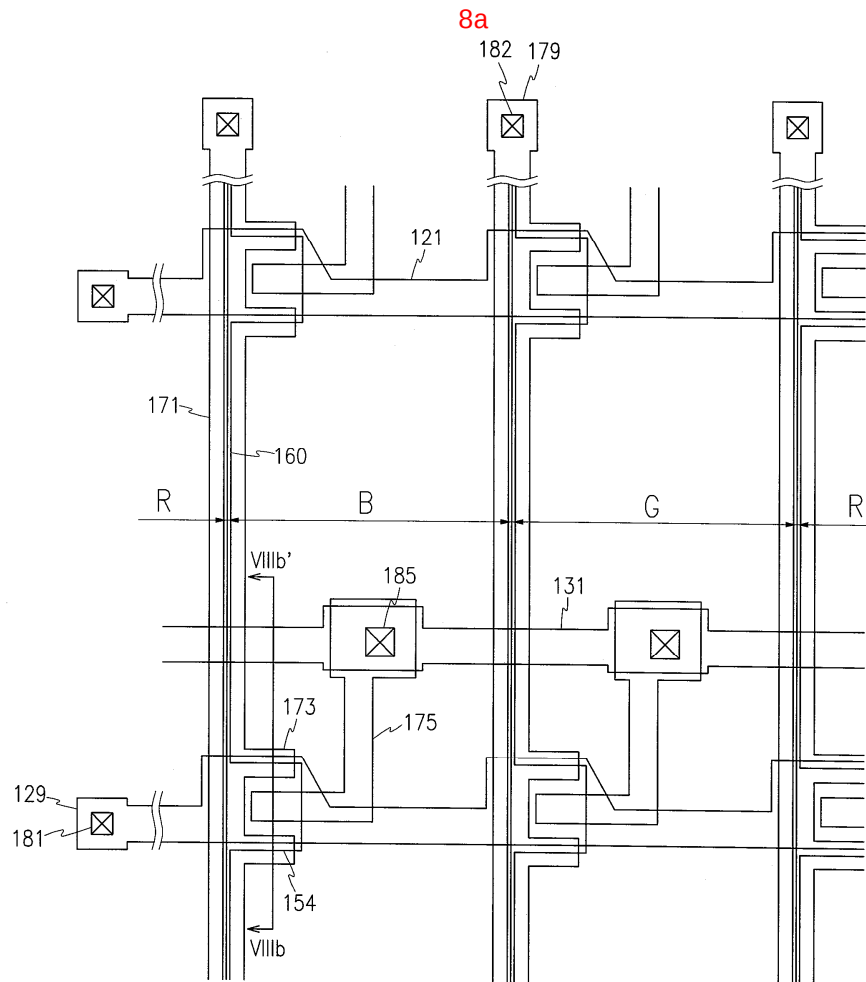


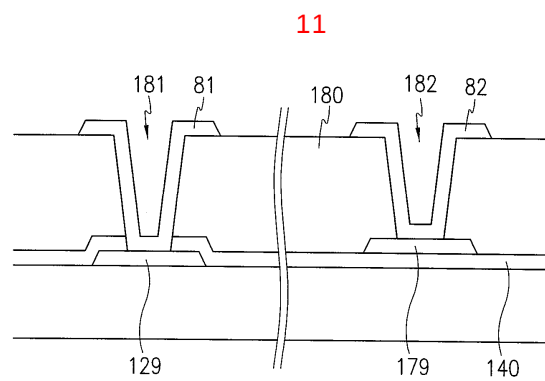
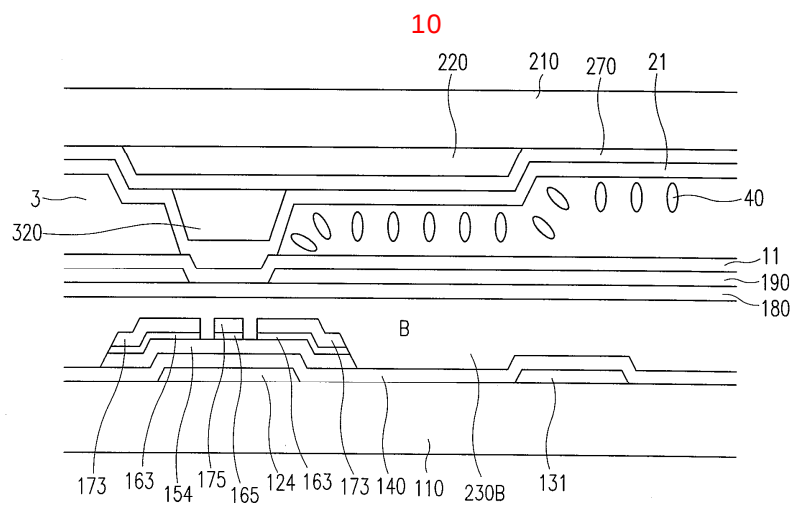
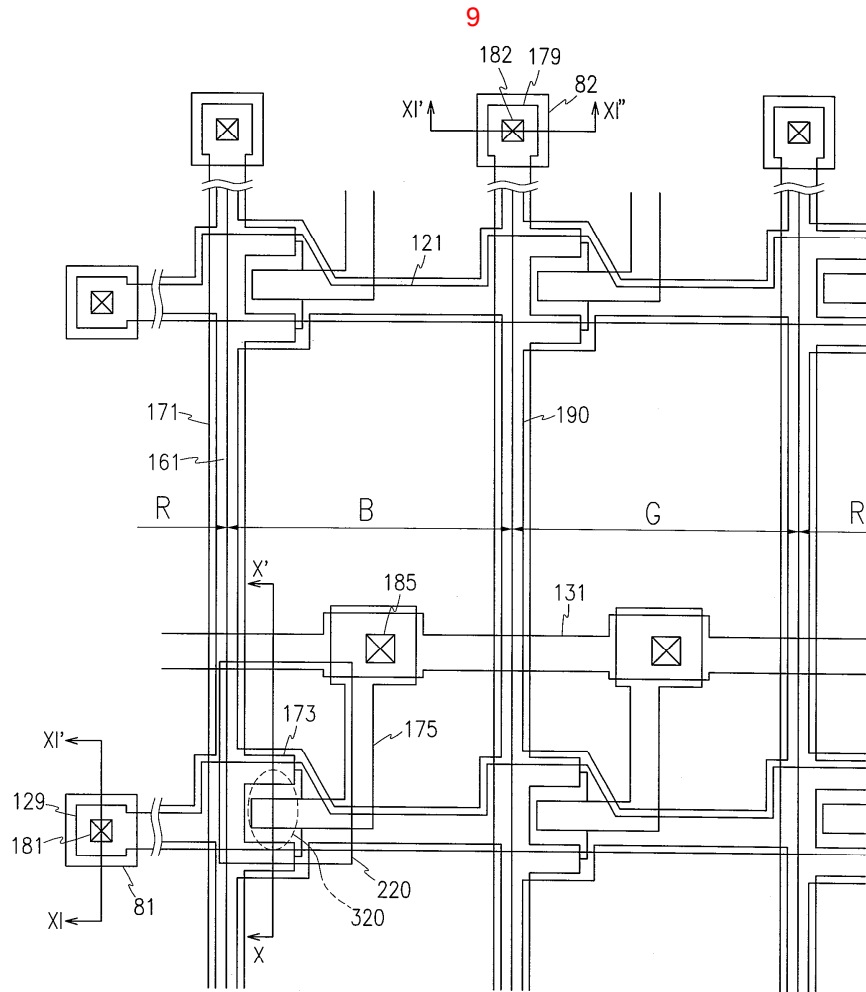
7a

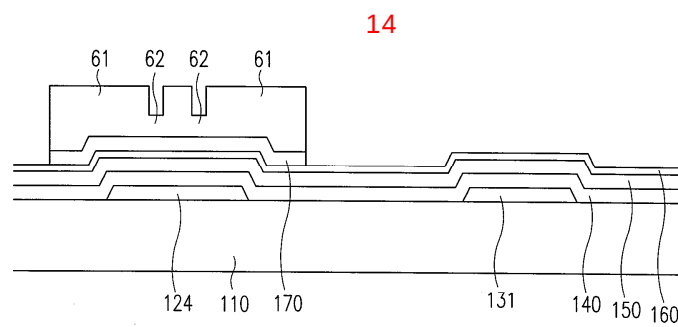
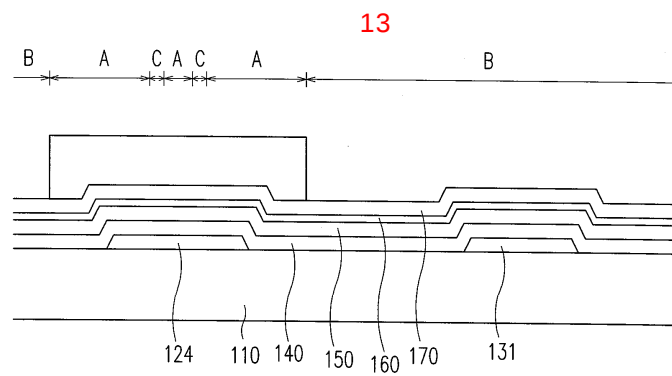
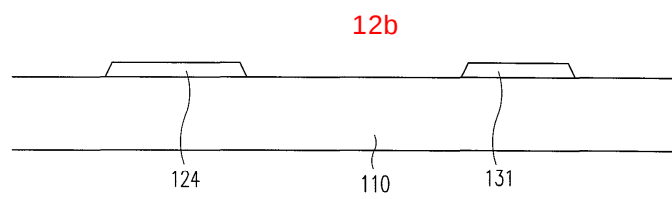
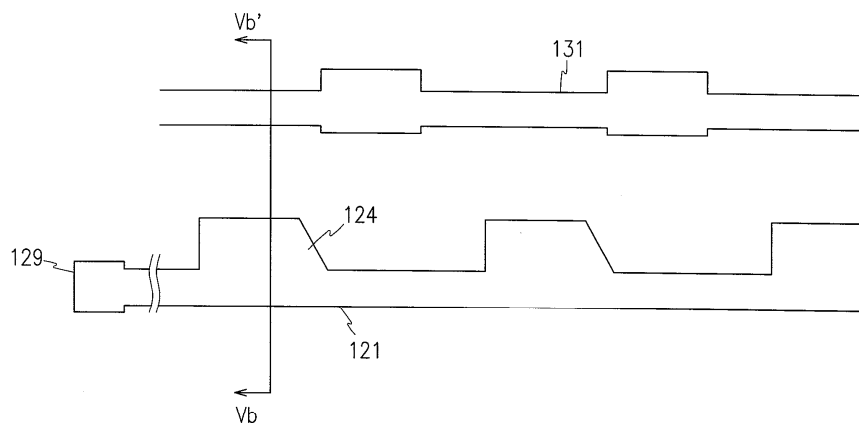
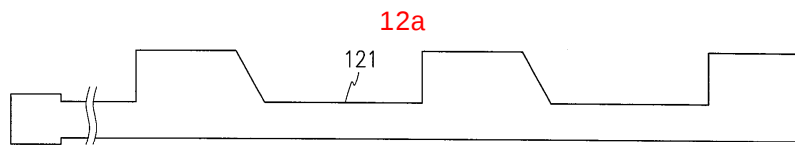


7b

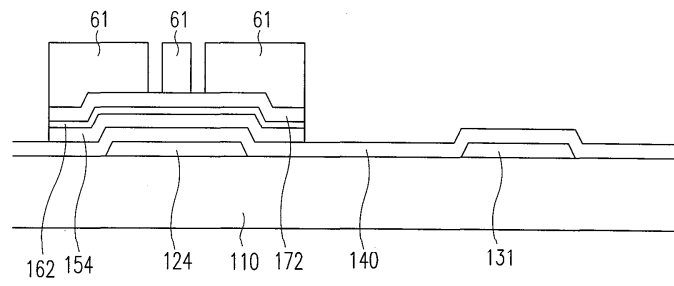




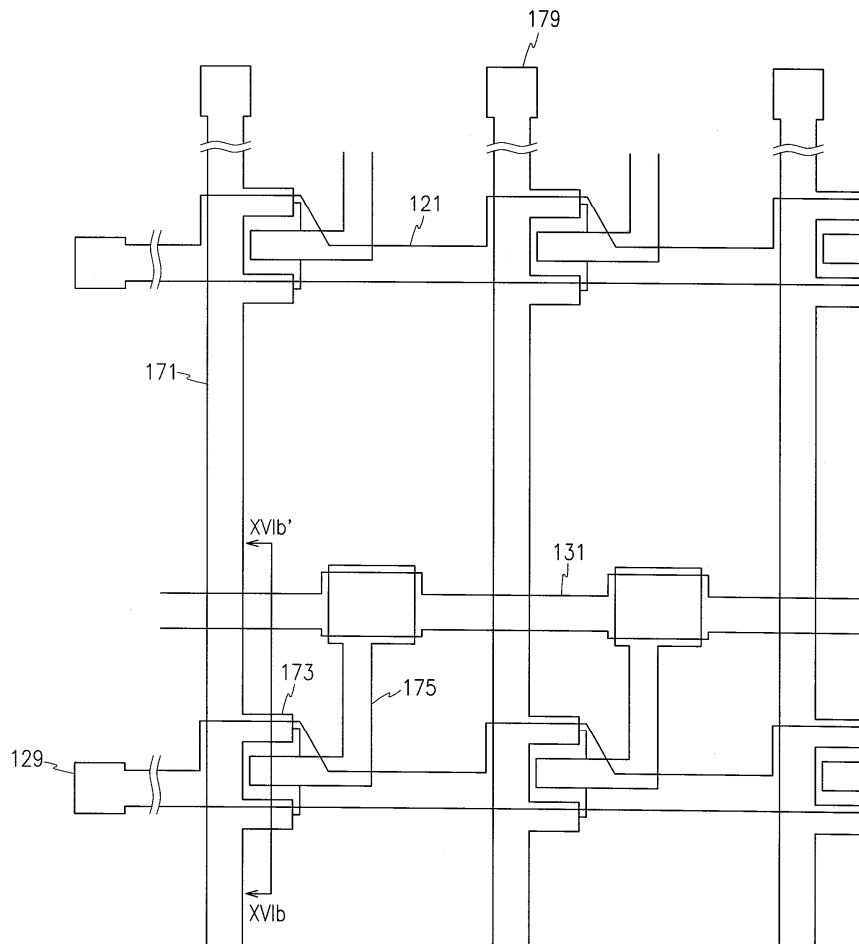




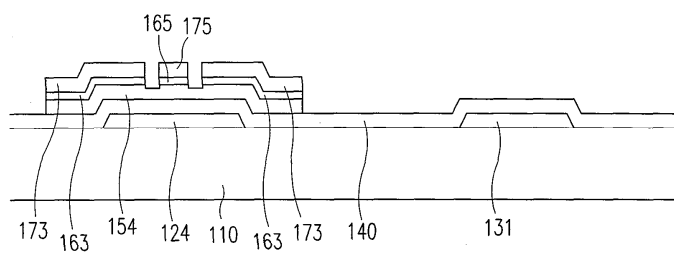
15

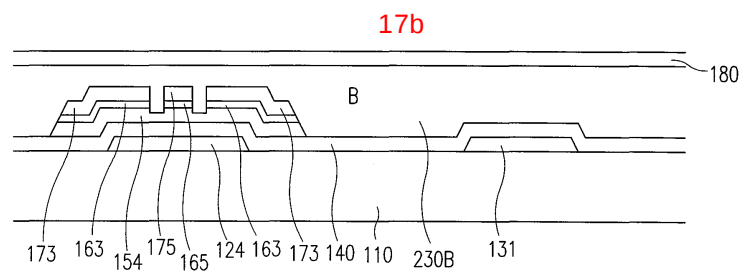
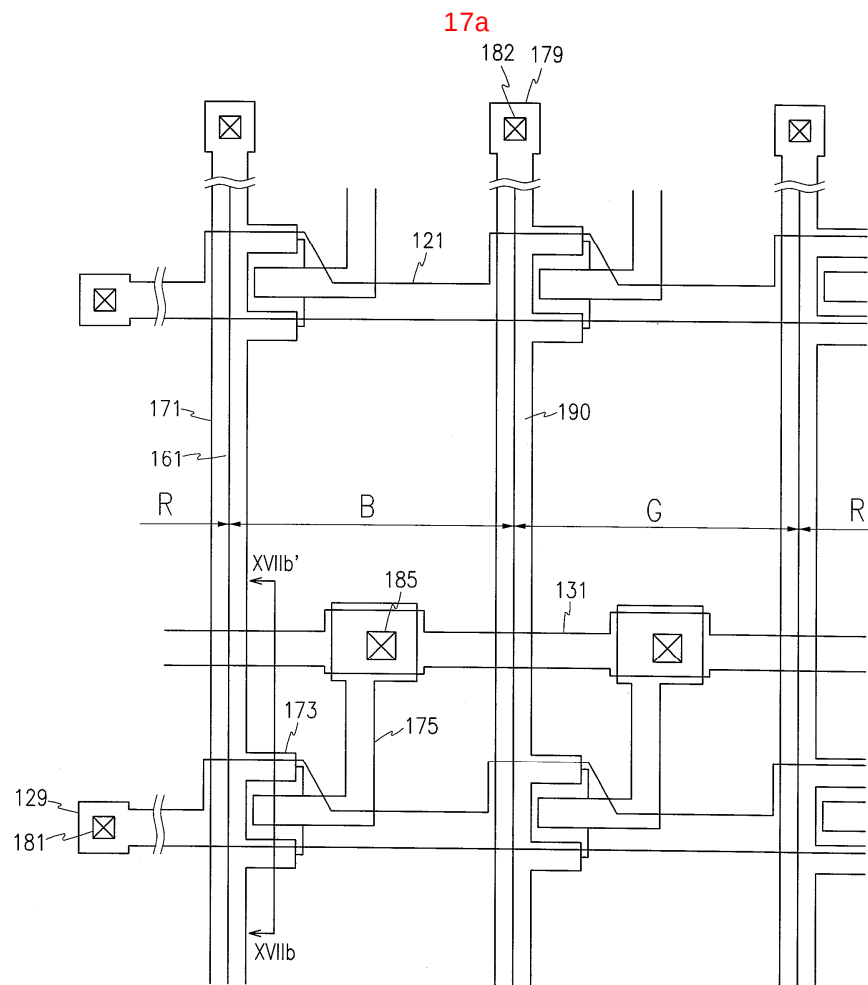


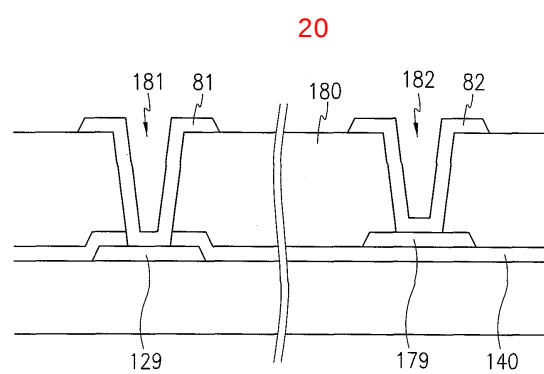
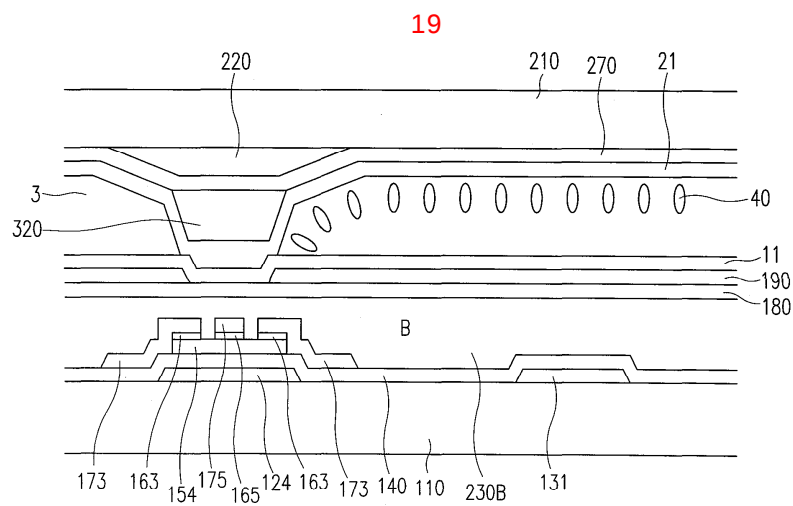
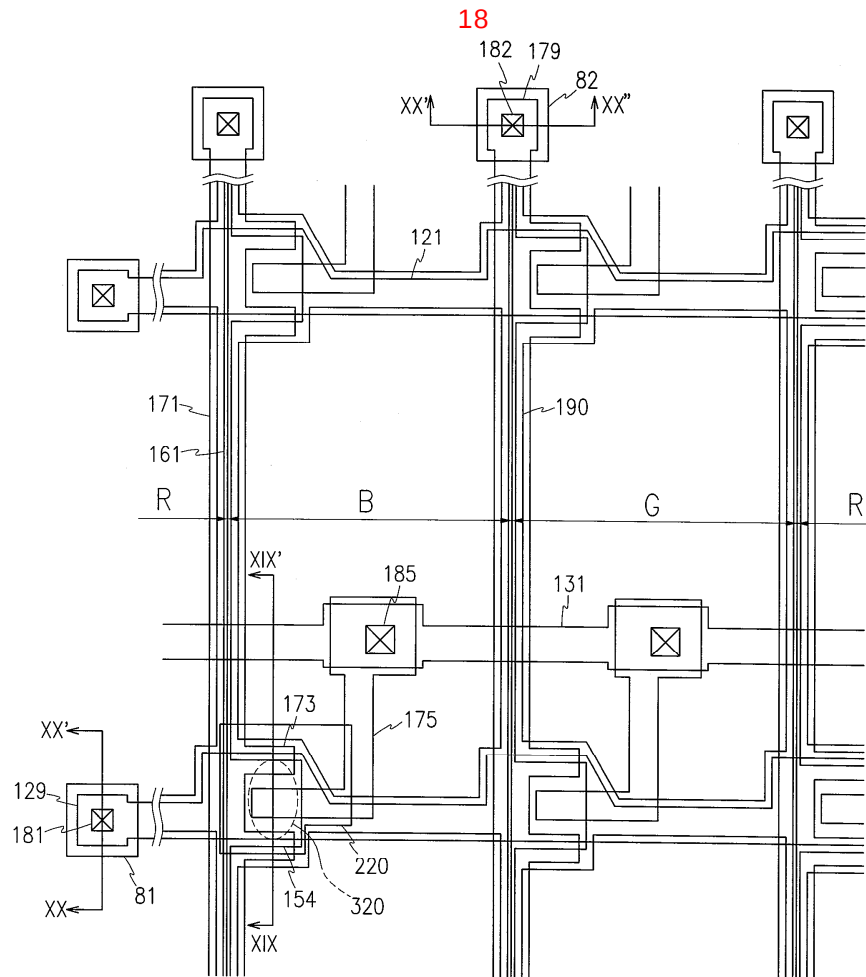
16a

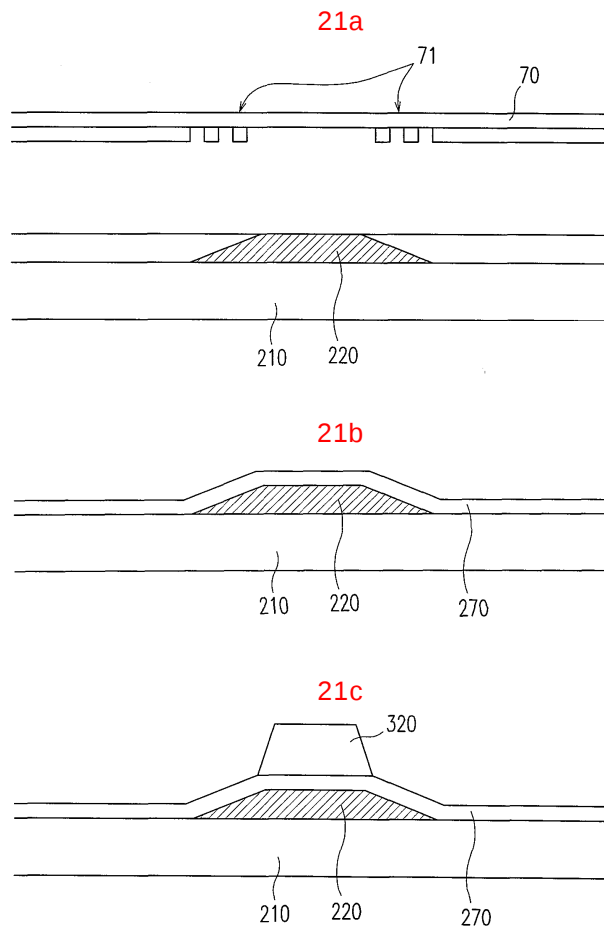


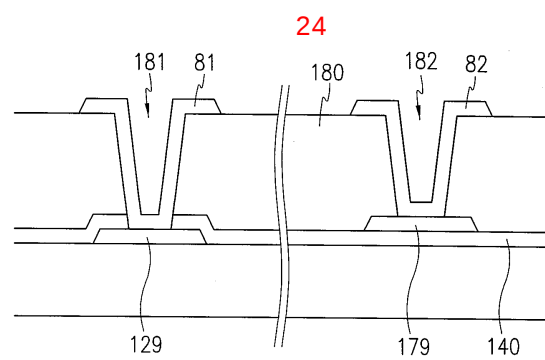
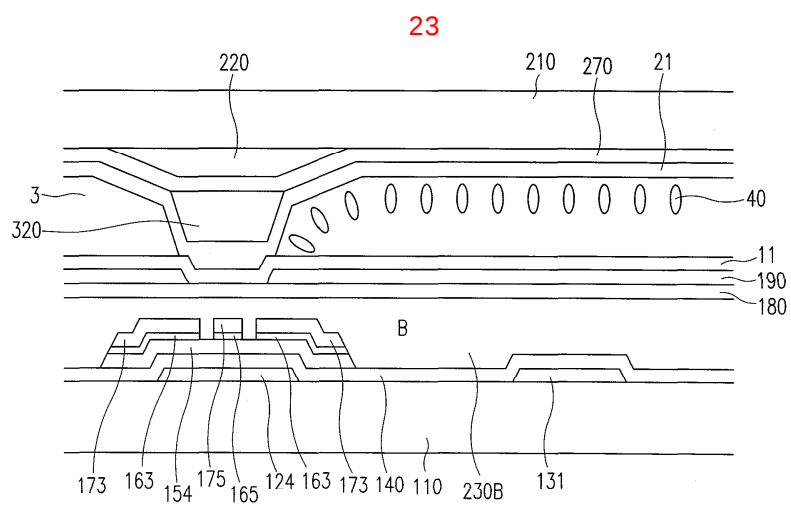
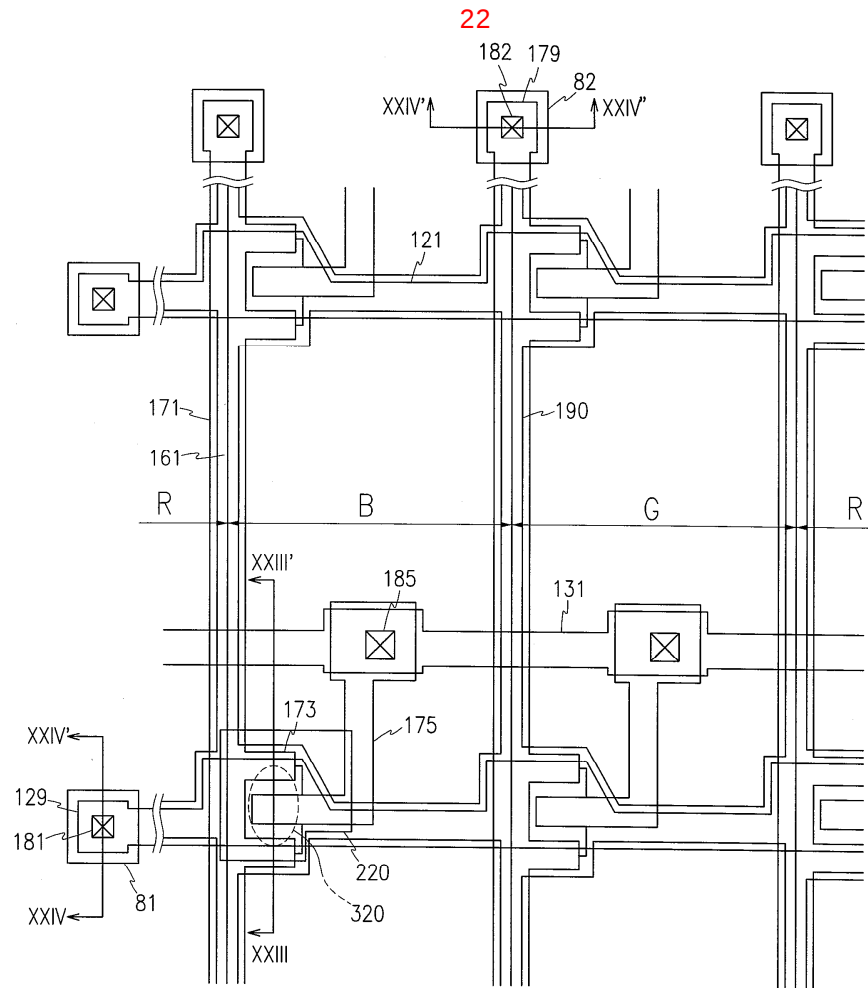
16b

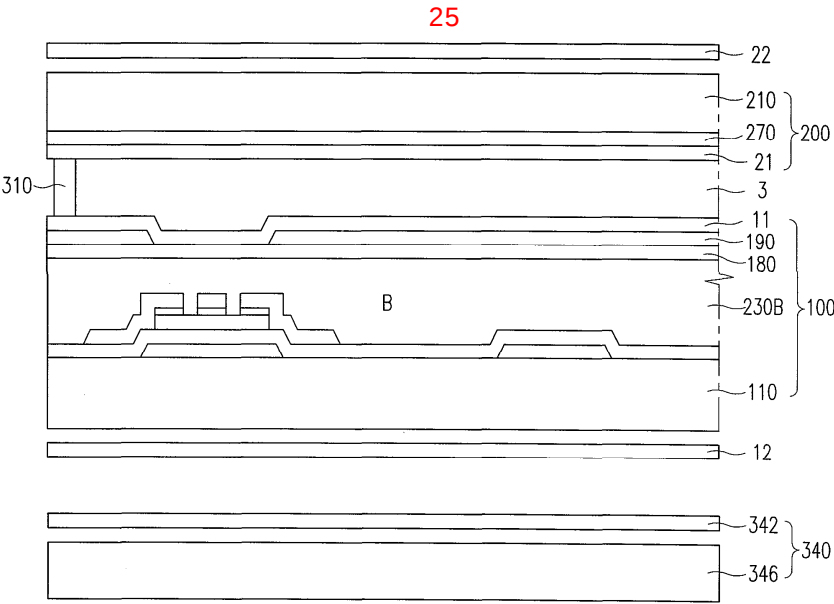












专利名称(译)	显示装置用显示面板和包括显示面板的液晶显示装置		
公开(公告)号	KR1020040107674A	公开(公告)日	2004-12-23
申请号	KR1020030036706	申请日	2003-06-09
[标]申请(专利权)人(译)	三星电子株式会社		
申请(专利权)人(译)	三星电子有限公司		
当前申请(专利权)人(译)	三星电子有限公司		
[标]发明人	KIM DONGGYU		
发明人	KIM,DONGGYU		
IPC分类号	G02F1/1335 G02F1/1339 G02F1/139 G02F1/1368 G02F1/1337 G02F1/1343		
CPC分类号	G02F1/13394 G02F1/133512 G02F1/1393		
其他公开文献	KR101012784B1		
外部链接	Espacenet		

摘要(译)

目的：提供一种用于显示装置的显示面板和包括该显示面板的液晶显示器，以防止由于遮光膜的台阶高度而产生的光损失，同时通过形成具有遮光膜的遮光膜来最小化孔径比的降低。缓慢的倾斜。

